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Vishay Semiconductors

AUTOMOTIVE GRADE

RoHS

COMPLIANT

HALOGEN FREE

GREEN

(5-2008)

## Single-Line Bidirectional ESD-Protection Diode in DFN1006-2B





**MARKING** (example only)



Bar = pin 1 marking X = date code YY = type code (see table below)

#### **LINKS TO ADDITIONAL RESOURCES**







#### **FEATURES**

- Compact DFN1006-2B package
- Low package height < 0.5 mm
- 1-line bidirectional ESD-protection
- AEC-Q101 qualified available
- Working range ±14 V; ± 28 V
- ESD immunity acc. IEC 61000-4-2 ±15 kV to ±30 kV contact discharge ±15 kV to ±30 kV air discharge
- Lead plating: Sn (e3)
- Soldering can be checked by standard vision inspection
- AOI = Automated Optical Inspection
- Material categorization: for definitions of compliance please see <a href="https://www.vishav.com/doc?99912">www.vishav.com/doc?99912</a>

#### **Soldering Recommendations for DFN Packages:**

please see Application Note: www.vishav.com/doc?86198

CE	=	
	A	

ORDERING INFORMATION						
	ENVIRONMENTAL AND QUALITY CODE					
PART NUMBER (EXAMPLE)	I FAD (Ph)-FREE TIME		10K PER 7" REEL (8 mm TAPE)	ORDERING CODE (EXAMPLE)		
		GREEN		MOQ = 10K/BOX		
VMMBZ16C1DD1	-	G	3	-08	VMMBZ16C1DD1-G3-08	
VMMBZ16C1DD1	Н	G	3	-08	VMMBZ16C1DD1HG3-08	

PACKAGE DATA								
DEVICE NAME	PACKAGE NAME	TYPE CODE	WEIGHT	MOLDING COMPOUND FLAMMABILITY RATING	MOISTURE SENSITIVITY LEVEL	SOLDERING CONDITIONS		
VMMBZ16C1DD1	DFN1006-2B	2Y	0.83 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	Peak temperature max. 260 °C		
VMMBZ33C1DD1	DFN1006-2B	2N	0.83 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	Peak temperature max. 260 °C		

# VMMBZ16C1DD1 to VMMBZ33C1DD1

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<b>ABSOLUTE MAXIMU</b> (T <sub>amb</sub> = 25 °C, unless of	JM RATINGS VMMBZ16C1DD1 otherwise specified)			
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Acc. IEC 61000-4-5, 8/20 µs/single shot	I <sub>PPM</sub>	4	Α
Peak pulse power	Acc. IEC 61000-4-5, 8/20 μs/single shot <sup>(1)</sup>	P <sub>PP</sub>	108	W
Peak pulse current	t <sub>p</sub> = 10/1000 μs <sup>(1)</sup>	I <sub>PPM</sub>	0.65	Α
Peak pulse power	t <sub>p</sub> = 10/1000 μs <sup>(1)</sup>	P <sub>PP</sub>	15	W
CCD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses (1)	V	30	kV
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses (1)	$V_{ESD}$	30	kV
Operating temperature	Junction temperature	TJ	-55 to +150	°C
Storage temperature		T <sub>sta</sub>	-55 to +150	°C

<b>ABSOLUTE MAXIMUM RATINGS</b> VMMBZ33C1DD1 (T <sub>amb</sub> = 25 °C, unless otherwise specified)						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Acc. IEC 61000-4-5, 8/20 μs/single shot	I <sub>PPM</sub>	1.7	Α		
Peak pulse power	Acc. IEC 61000-4-5, 8/20 μs/single shot <sup>(1)</sup>	P <sub>PP</sub>	100	W		
Peak pulse current	t <sub>p</sub> = 10/1000 μs <sup>(1)</sup>	I <sub>PPM</sub>	0.3	Α		
Peak pulse power	t <sub>p</sub> = 10/1000 μs <sup>(1)</sup>	P <sub>PP</sub>	15	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses (1)	V	15	kV		
E3D Illillullity	Air discharge acc. IEC 61000-4-2; 10 pulses (1)	$V_{ESD}$	15	kV		
Operating temperature	Junction temperature	TJ	-55 to +150	°C		
Storage temperature		T <sub>stg</sub>	-55 to +150	°C		

<b>ELECTRICAL CHARACTERISTICS</b> VMMBZ16C1DD1 (T <sub>amb</sub> = 25 °C, unless otherwise specified)							
PARAMETER	TEST CONDITIONS / REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Protection paths	Number of lines which can be protected	N <sub>channel</sub>	ı	-	1	lines	
Reverse stand off voltage	Max. reverse working voltage	$V_{RWM}$	-	-	14	V	
Reverse voltage	At I <sub>R</sub> = 0.1 μA	$V_R$	14	-	-	V	
Develope account	At V <sub>R</sub> = 14 V	I <sub>R</sub>	-	< 1	10	nA	
Reverse current	At $V_R = 14 \text{ V}$ ; $T_J = 150 ^{\circ}\text{C}^{(1)}$		-	0.06	10	μA	
Reverse breakdown voltage	At I <sub>R</sub> = 1 mA	V <sub>BR</sub>	16.2	16.7	17.3	V	
heverse breakdown voltage	At $I_R = 1$ mA; $T_J = -40$ °C to $+150$ °C $^{(1)}$		15	-	18.7	V	
Deverse elemning veltage	At $I_{PP} = I_{PPM} = 4 \text{ A}$ , $t_p = 8/20 \mu\text{s}$	V <sub>C</sub>	20	23.7	27	V	
Reverse clamping voltage	$t_p = 100 \text{ ns (TLP)}; I_{TLP} = 16 \text{ A}^{(1)}$	$V_{C\_TLP}$	-	26	-	V	
Dynamic resistance	t <sub>p</sub> = 100 ns (TLP) <sup>(1)</sup>	r <sub>dyn</sub>	-	0.55	-	Ω	
Capacitance	At V <sub>R</sub> = 0 V; f = 1 MHz	C <sub>D</sub>	12	14.5	17	pF	

ELECTRICAL CHARA (T <sub>amb</sub> = 25 °C, unless oth	CTERISTICS VMMBZ33C1DD1 nerwise specified)					
PARAMETER	TEST CONDITIONS / REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N <sub>channel</sub>	-	-	1	lines
Reverse stand off voltage	Max. reverse working voltage	$V_{RWM}$	-	-	28	V
Reverse voltage	At I <sub>R</sub> = 0.1 μA	$V_R$	28	-	-	V
Reverse current	At V <sub>R</sub> = 28 V	I <sub>R</sub>	-	< 1	10	nA
neverse current	At $V_R = 28 \text{ V}$ ; $T_J = 150  ^{\circ}\text{C}^{(1)}$		-	0.1	10	μΑ
Daviera brackdown valtage	At I <sub>R</sub> = 1 mA		32.7	33.7	34.8	V
Reverse breakdown voltage	At $I_R = 1$ mA; $T_J = -40$ °C to $+150$ °C $^{(1)}$	$V_{BR}$	30	-	39.7	V
Deverse elemning veltage	At $I_{PP} = I_{PPM} = 1.7 \text{ A}$ , $t_p = 8/20 \mu\text{s}$	V <sub>C</sub>	40	49	59	V
Reverse clamping voltage	$t_p = 100 \text{ ns (TLP)}; I_{\_TLP} = 16 \text{ A}^{(1)}$	V <sub>C_TLP</sub>	-	88	-	V
Dynamic resistance	t <sub>p</sub> = 100 ns (TLP) <sup>(1)</sup>	r <sub>dyn</sub>	-	3.3	-	Ω
Capacitance	At $V_R = 0 \text{ V}$ ; $f = 1 \text{ MHz}$	C <sub>D</sub>	6	8	10	pF

### Note

<sup>(1)</sup> Guaranteed by design. Tested during device characterization

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f = 1 MHz

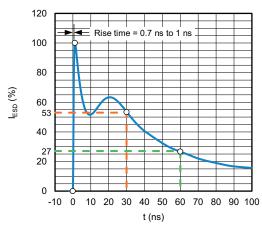
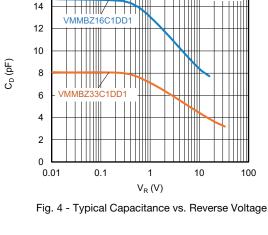


Fig. 1 - ESD Discharge Current Wave Form Acc. IEC 61000-4-2  $(330 \Omega / 150 pF)$ 



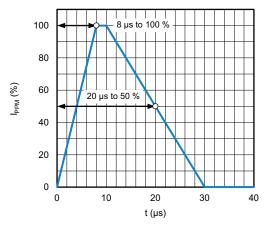


Fig. 2 - 8/20 µs Peak Pulse Current Wave Form Acc. IEC 61000-4-5

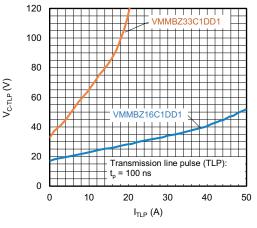


Fig. 5 - Typical Clamping Voltage vs. Peak Pulse Current

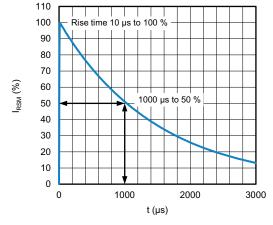


Fig. 3 - 10/1000 µs Peak Pulse Current Wave Form

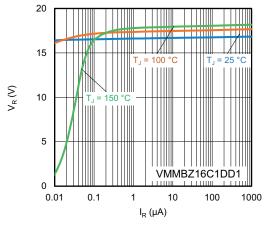


Fig. 6 - Typical Reverse Voltage vs. Reverse Current

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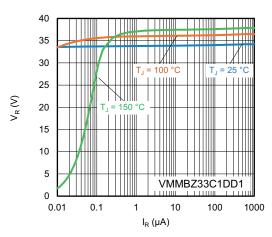


Fig. 7 - Typical Reverse Voltage vs. Reverse Current

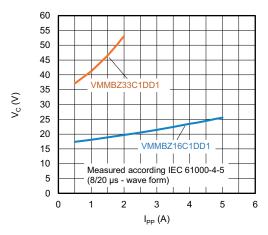


Fig. 8 - Typical Peak Clamping Voltage vs. Peak Pulse Current

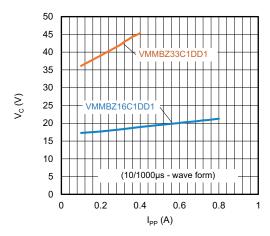


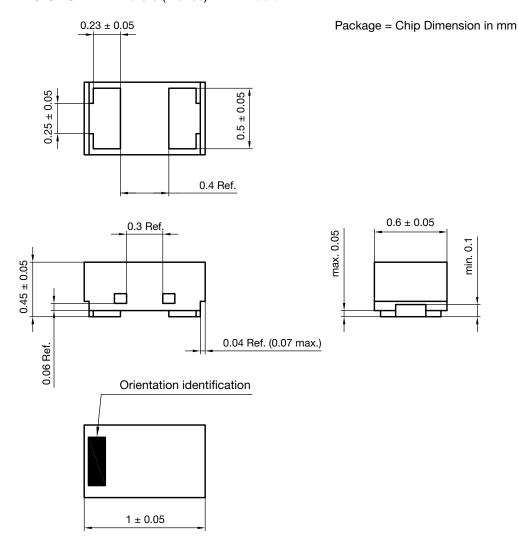
Fig. 9 - Typical Peak Clamping Voltage vs. Peak Pulse Current

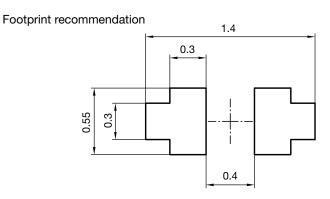




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### PACKAGE DIMENSIONS in millimeters (inches): DFN1006-2B



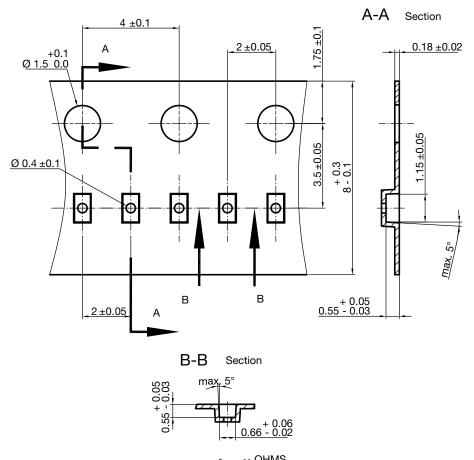


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#### **CARRIER TAPE DFN1006-2B**



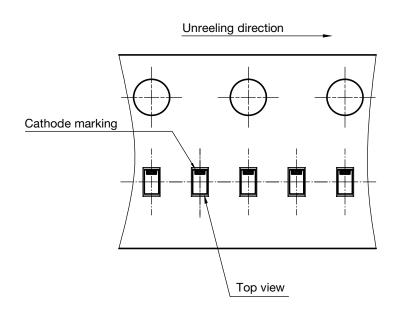
S8-V-3906.04-063 (4) created 28.10.2019

S8-V-3906.04-064 (4)

created 28.10.2019

surface resistance:  $10^5$  -  $10^{11} \frac{OHMS}{SQ}$ Cummulative tolerances of 10 sprocket holes is  $\pm 0.2$  mm

### **ORIENTATION IN CARRIER TAPE DFN1006-2B**



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